

Change in the parameters of electron-irradiated 4H-SiC Schottky diodes as a function of the time during low-temperature isothermal annealing

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Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons

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Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0.9 MeV electrons

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Dependence of the carrier removal rate in 4H-SiC PN structures on irradiation temperature

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Influence of the proton irradiation temperature on the characteristics of high-power high-voltage silicon carbide schottky diodes

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Low-temperature annealing of lightly doped n-4H-SiC layers after irradiation with fast electrons

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SiC schottky diode rectifier bridge represented as the diffusion-welded stack

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